

## N-Channel 60-V (D-S) MOSFET

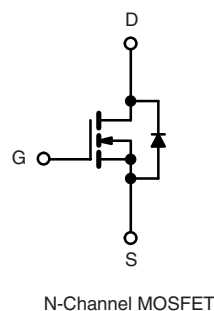
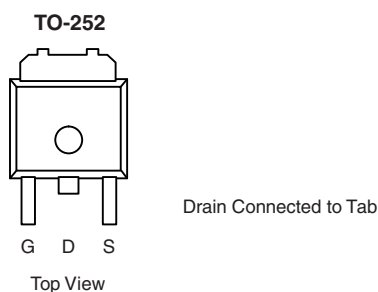
PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>a</sup>
60	0.025 at $V_{GS} = 10$ V	35
	0.030 at $V_{GS} = 4.5$ V	30

### FEATURES

- TrenchFET<sup>®</sup> Power MOSFET
- 175 °C Junction Temperature



Available  
**RoHS\***  
 COMPLIANT



ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted				
Parameter		Symbol	Limit	Unit
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current ( $T_J = 175$ °C) <sup>b</sup>	$T_C = 25$ °C	$I_D$	35	A
	$T_C = 100$ °C		28	
Pulsed Drain Current		$I_{DM}$	100	
Continuous Source Current (Diode Conduction)		$I_S$	23	
Avalanche Current		$I_{AS}$	20	
Single Avalanche Energy (Duty Cycle $\leq 1$ %)	$L = 0.1$ mH	$E_{AS}$	20	mJ
Maximum Power Dissipation	$T_C = 25$ °C	$P_D$	100	W
	$T_A = 25$ °C		3 <sup>a</sup>	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 10$ sec	$R_{thJA}$	18	22	°C/W
	Steady State		40	50	
Maximum Junction-to-Case		$R_{thJC}$	3.2	4	

Notes:

a. Surface Mounted on 1" x 1" FR4 board,  $t \leq 10$  sec.

<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ <sup>a</sup>	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0	2.0	3.0	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			250	
On-State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	50			A
Drain-Source On-State Resistance <sup>b</sup>	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 15\text{ A}$		0.025	0.031	$\Omega$
		$V_{GS} = 10\text{ V}, I_D = 15\text{ A}, T_J = 125\text{ }^\circ\text{C}$			0.055	
		$V_{GS} = 10\text{ V}, I_D = 15\text{ A}, T_J = 175\text{ }^\circ\text{C}$			0.069	
		$V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$		0.030	0.045	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$		20		S
<b>Dynamic<sup>a</sup></b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		670		$\text{pF}$
Output Capacitance	$C_{oss}$			140		
Reverse Transfer Capacitance	$C_{rss}$			60		
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 23\text{ A}$		11	17	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			3		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			3		
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 1.3\text{ }\Omega$ $I_D \cong 23\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		8	15	ns
Rise Time <sup>c</sup>	$t_r$			15	25	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			30	45	
Fall Time <sup>c</sup>	$t_f$			25	40	
<b>Source-Drain Diode Ratings and Characteristics</b> ( $T_C = 25\text{ }^\circ\text{C}$ )						
Pulsed Current	$I_{SM}$				50	A
Diode Forward Voltage	$V_{SD}$	$I_F = 15\text{ A}, V_{GS} = 0\text{ V}$		1.0	1.5	V
Reverse Recovery Time	$t_{rr}$	$I_F = 15\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		30	60	ns

## Notes:

- For design aid only; not subject to production testing.
- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C unless noted



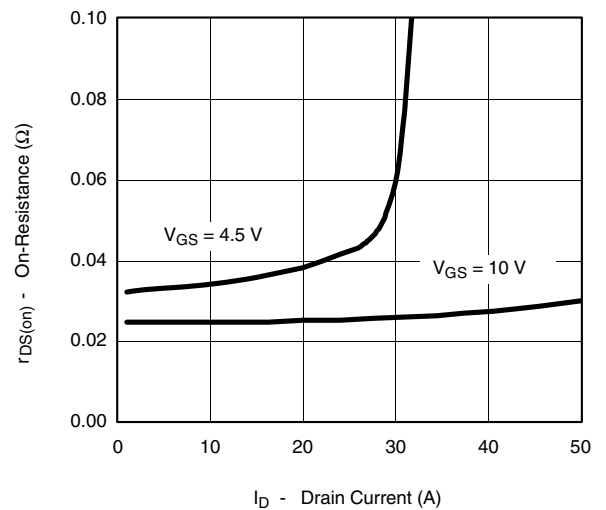
**Output Characteristics**



**Transfer Characteristics**



**Transconductance**



**On-Resistance vs. Drain Current**

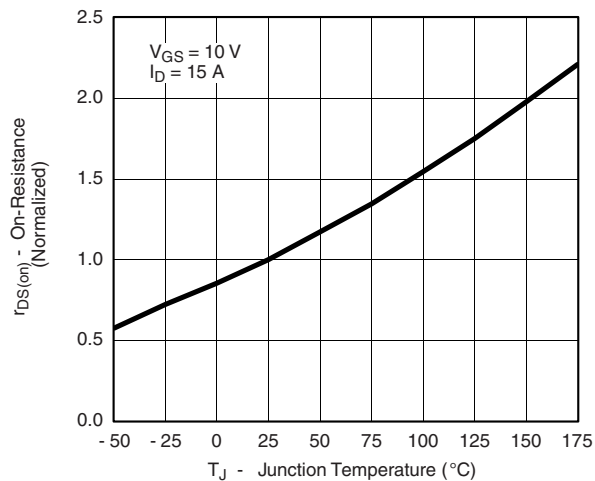


**Capacitance**

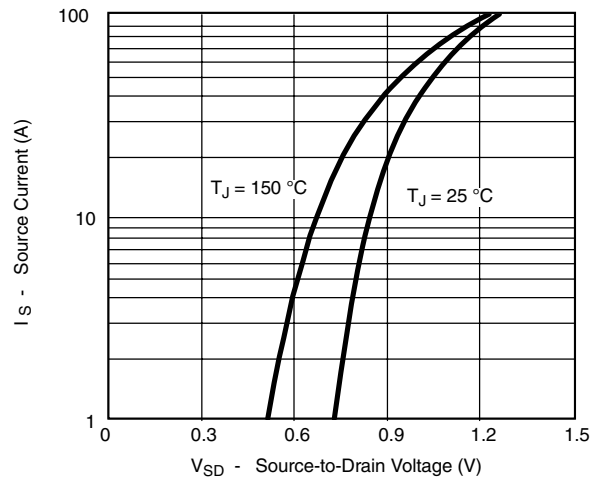


**Gate Charge**

**TYPICAL CHARACTERISTICS** 25 °C unless noted



**On-Resistance vs. Junction Temperature**



**Source-Drain Diode Forward Voltage**

**THERMAL RATINGS**



TA - Ambient Temperature (°C)  
**Maximum Drain Current vs. Ambient Temperature**



V<sub>DS</sub> - Drain-to-Source Voltage (V)  
\*V<sub>GS</sub> > minimum V<sub>GS</sub> at which r<sub>DS(on)</sub> is specified  
**Safe Operating Area**



**Normalized Thermal Transient Impedance, Junction-to-Case**

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